

## Silicon NPN Power Transistor

#### **DESCRIPTION**

- · High Collector-Emitter Breakdown Voltage-
  - : V<sub>(BR)CEO</sub>= 400V(Min)
- · High Switching Speed
- · High Reliability

#### **APPLICATIONS**

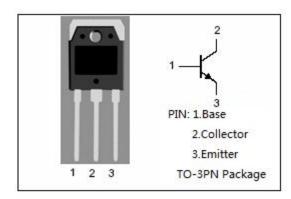
- · Switching regulators
- Ultrasonic generators
- · High frequency inverters
- General purpose power amplifiers

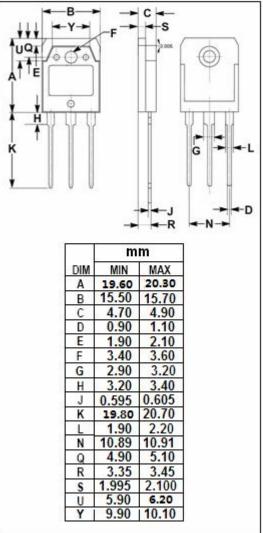
### ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage 500		V
Vceo	Collector-Emitter Voltage 400		V
V <sub>CEO(SUS)</sub>	Collector-Emitter Voltage 400		V
V <sub>EBO</sub>	Emitter-Base Voltage 7		V
Ic	Collector Current-Continuous	15	А
I <sub>B</sub>	Base Current-Continuous	5	А
Pc	Collector Power Dissipation @ T <sub>C</sub> =25 °C	80	W
TJ	Junction Temperature	150	$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range -65~150		$^{\circ}$

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER		UNIT
R <sub>th j-c</sub>	Thermal Resistance,Junction to Case	1.56	°C/W





## **Ordering Information**

Product	Package	Packaging
2LSC3320T4TL	TO-3PN	Tube

V01 1



#### **ELECTRICAL CHARACTERISTICS**

#### $T_{\text{C}}$ =25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 10mA ; I <sub>B</sub> = 0	400			٧
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 50mA ; I <sub>B</sub> = 0	400			V
V <sub>(BR)CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 1mA ; I <sub>E</sub> = 0	500			V
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 1mA; I <sub>C</sub> = 0	7			V
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 1.2A			1.0	V
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage	I <sub>C</sub> = 6A; I <sub>B</sub> = 1.2A			1.5	V
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 500V ; I <sub>E</sub> = 0			1.0	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 7V; I <sub>C</sub> = 0			1.0	mA
h <sub>FE</sub>	DC Current Gain	Ic= 6A; Vc= 5V	10			
Switching ti	mes			•		•
t <sub>on</sub>	Turn-on Time				0.5	μs

t <sub>on</sub>	Turn-on Time	I <sub>C</sub> = 7.5A , I <sub>B1</sub> = 1.5A; I <sub>B2</sub> = -3A R <sub>L</sub> = 20 Ω ;P <sub>W</sub> =20 μ s Duty≤2%		0.5	μs
t <sub>stg</sub>	Storage Time			1.5	μs
t <sub>f</sub>	Fall Time			0.15	μs

V01 2

# **X-ON Electronics**

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by SPS manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H MJ15024/WS MJ15025/WS BC546/116 BC556/FSC BC557/116 BSW67A HN7G01FU-A(T5L,F,T NJVMJD148T4G NSVMMBT6520LT1G NTE187A NTE195A NTE2302 NTE2302 NTE2330 NTE2353 NTE316 IMX9T110 NTE63 NTE65 C4460 SBC846BLT3G 2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA1727TLP 2SA2126-E 2SB1202T-TL-E 2SB1204S-TL-E 2SC5488A-TL-H 2SD2150T100R SP000011176 FMC5AT148 2N2369ADCSM 2SB1202S-TL-E 2SC2412KT146S 2SC4618TLN 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E BC557B TTC012(Q) BULD128DT4 JANTX2N3810 Jantx2N5416 US6T6TR KSF350 068071B